

RPC 2020



Virtual Research Presentation Conference

Ka-band GaN-based Solid-State Power Amplifier for Deep-Space Telecommunications

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Program: Strategic Initiative

Assigned Presentation #RPC-283



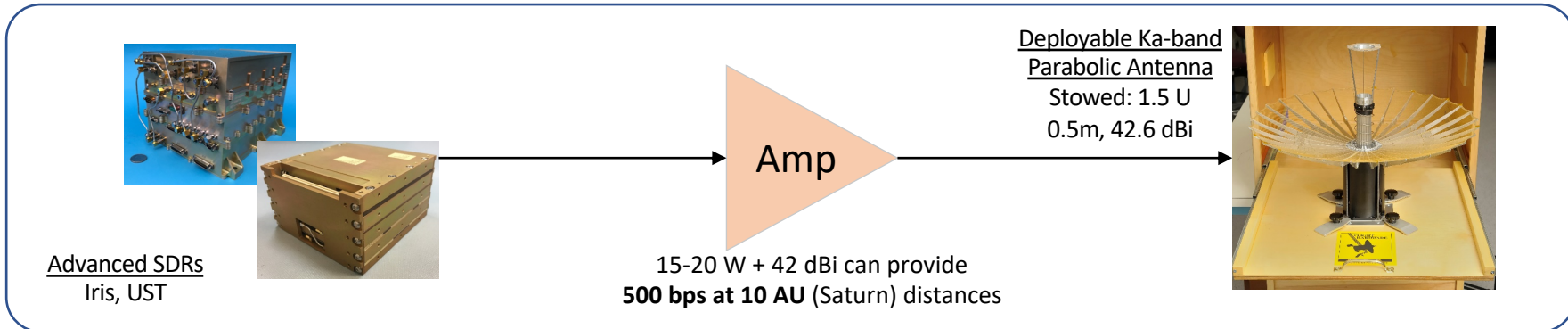
Jet Propulsion Laboratory
California Institute of Technology



Abstract

The objective of this research was to investigate the path towards achieving a highly efficient Ka-band (31.8 to 32.3 GHz) solid-state power amplifier for deep-space telecommunications applications. The goal of this 3-year task is to develop a **high-efficiency power amplifier that can provide approximately 500 bps of telemetry downlink to the DSN at a range of 10 Astronomical Units** in conjunction with the 42 dBi gain from the Ka-band Parabolic Deployable Antenna. The development of such a Ka-band SSPA fills the gap between various other investments in advanced software-defined radios (SDRs) and deployable antenna technologies.

The main objectives for Year-2 of this 3-year task was to **1)** complete the design of a high-efficiency monolithic GaN amplifier MMIC for a target fabrication start-date of January 2020, **2)** continue the investigation of an alternate discrete approach to providing impedance matching, and **3)** complete the optimization of the spatial power-combiner and fabricate it for test. 2020 has been a challenging year with the COVID-19 pandemic affecting various sectors, introducing large uncertainties for fabrication plans and delivery dates. Some course corrections were necessary as a result, but many goals were still met despite the disturbance.





1. Spectrum allocation for deep-space comm

- S-band is effectively closed due to limited bandwidth
- X-band is getting crowded as current workhorse
- Ka-band remains largely unused despite advantages

S-band is **effectively closed** due to limited bandwidth and terrestrial interference

X-band is the current workhorse for deep space communication, but **getting crowded**

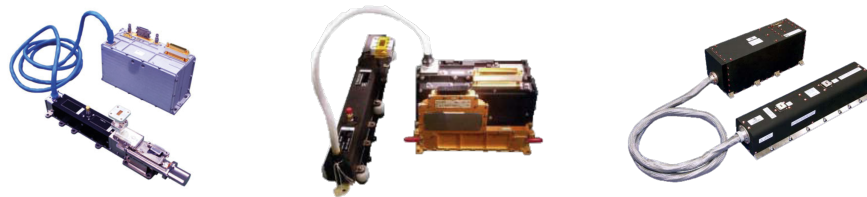
Ka-band is **largely unused**

- ~10x bandwidth capacity
- ~16x antenna gain efficiency
- ~4x radiometric precision



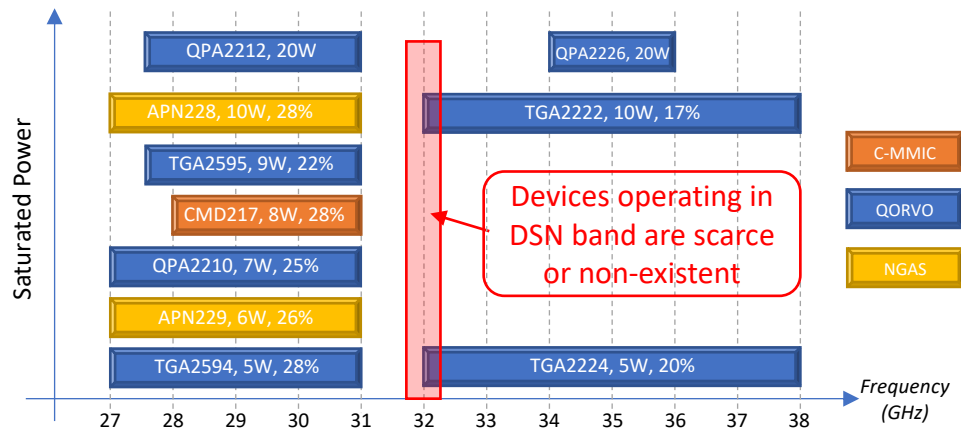
2. Disadvantages of vacuum-based amplifiers

- Mass/volume prohibitive on SmallSat platforms
- Requires extensive high-voltage expertise
- Sensitive to dynamic shock/vibration environments
- US manufacturing capability disappearing



3. No suitable commercial devices available today

- Vendors focus on wideband GaN devices
- Low efficiency < 30% to cover multi-GHz bandwidth
- Focus is NOT the DSN band (31.8-32.3 GHz)
 - 27-31 GHz: Satcom
 - 32-38 GHz: Radar, Terrestrial Comm, and EW



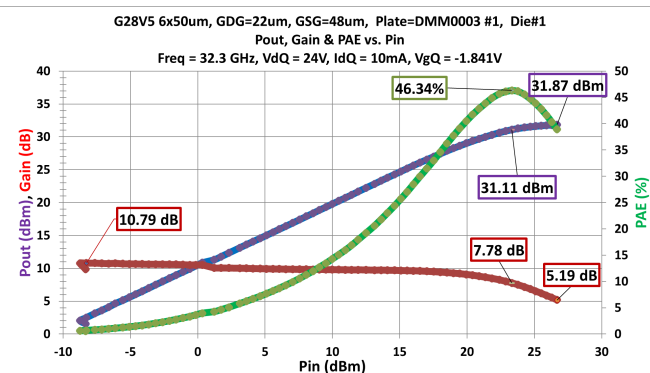
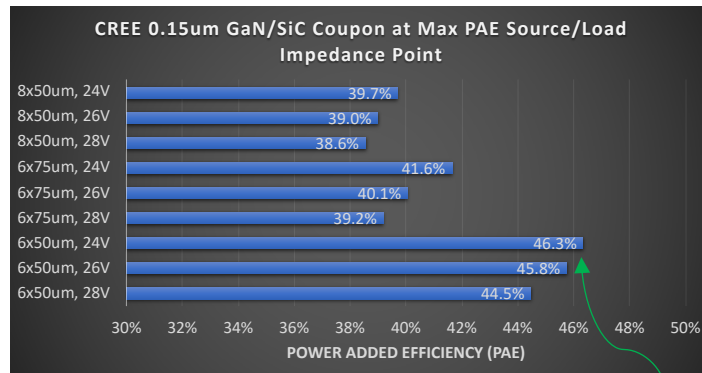


Monolithic GaN MMIC Approach

Develop harmonically-tuned GaN amplifier to optimize efficiency

- Recent advances on GaN processes provide shorter gate length
- Reduced parasitic reactance → higher frequency response
- Selected CREE/Wolfspeed's 150-nm GaN/SiC process
 - Highest output power and maturity amongst competitor processes

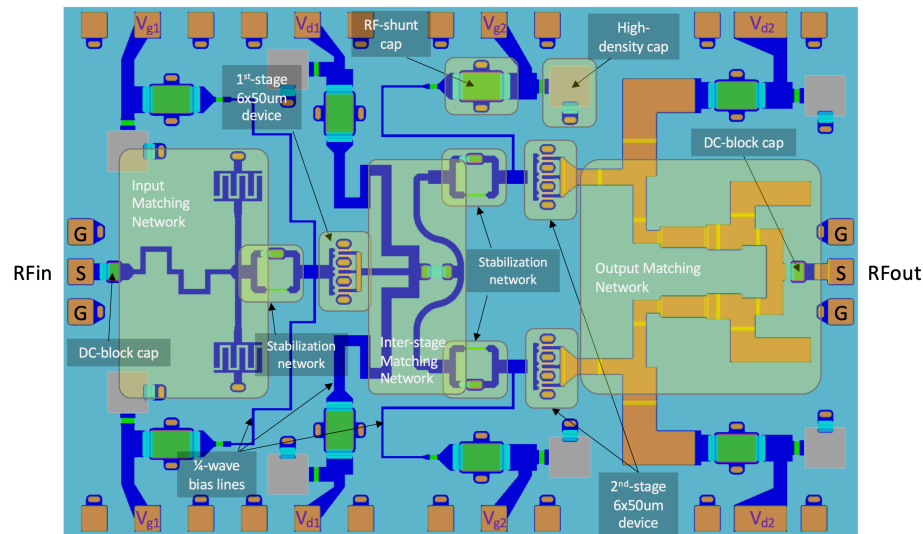
Performed harmonic source-/load-pull characterization to determine optimum impedances for peak efficiency



Highest PAE of 46.3% measured at 24V bias

Monolithic GaN MMIC Approach

Specification	As Designed
Topology:	2-stage Harmonic-Tuned IMN & OMN
Frequency:	31.8 to 32.3 GHz
Pout:	2.6 W (~34.1 dBm)
PAE:	35-37%
X/Y Size:	2x3 mm
S11 / S22:	-22.5 dB / -14.9 dB
S21:	20.8 dB
Bias:	+24 V @ 135 mA
Psat:	2.8 W (34.5 dBm)



Significance of Result:

- **Best-in-class PAE** using CREE's 150-nm GaN/SiC process providing tuned performance for the DSN's 31.8-32.3 GHz Ka-band downlink frequency allocation
- Similar technique employed on other GaN processes (HRL, OMMIC, NGAS) could potentially yield even higher efficiencies with future maturity

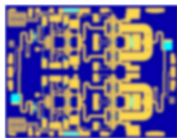
TGA2224
32 – 38 GHz 5 Watt GaN Amplifier



Key Features

- Frequency Range: 32 – 38 GHz
- P_{1dB} (P_{in}=21 dBm): > 37 dBm
- PAE (P_{in}=21 dBm): > 20 %
- Power Gain (P_{in}=21 dBm): > 16 dB
- Small Signal Gain: > 25 dB
- Bias (pushed): V₀ = 26 V, I₀ = 320 mA
- Bias (CW): V₀ = 24 V, I₀ = 320 mA
- Die Dimensions: 3.43 x 1.47 x 0.05 mm

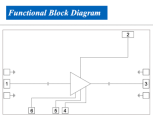
TGA2222
32 – 38 GHz 10 Watt GaN Amplifier



Key Features

- Frequency Range: 32 – 38 GHz
- P_{1dB} (P_{in}=24 dBm): > 40 dBm
- PAE (P_{in}=24 dBm): > 22 %
- Power Gain (P_{in}=24 dBm): > 16 dB
- Small Signal Gain: > 25 dB
- Bias (pushed): V₀ = 28 V, I₀ = 640 mA
- Bias (CW): V₀ = 24 V, I₀ = 640 mA
- Die Dimensions: 3.43 x 2.65 x 0.05 mm

CMD217
28-32 GHz GaN Power Amplifier



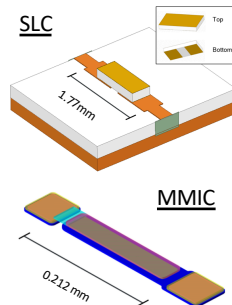
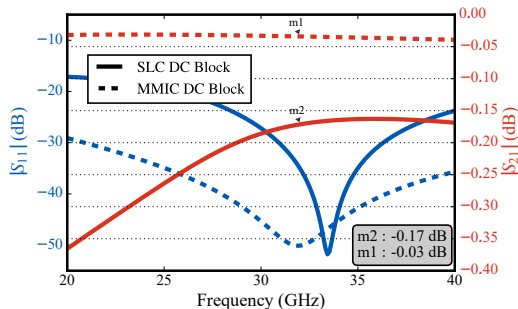
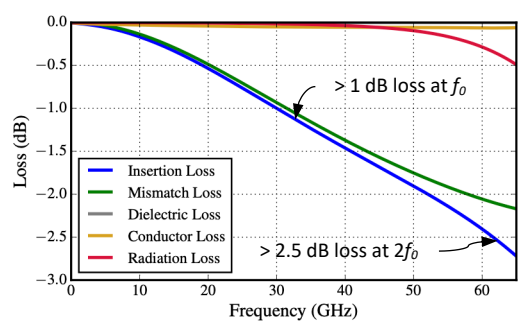
Parameter	Min	Typ	Max	Units
Frequency Range	28	32		GHz
Gain	20			dB
Input Return Loss	13			dB
Output Return Loss	15			dB
Output P1dB	36.7			dBm
PAE	29			dBm
Output IP3	41.5			dBm
Power Added Efficiency	32			%
Supply Current	580			mA



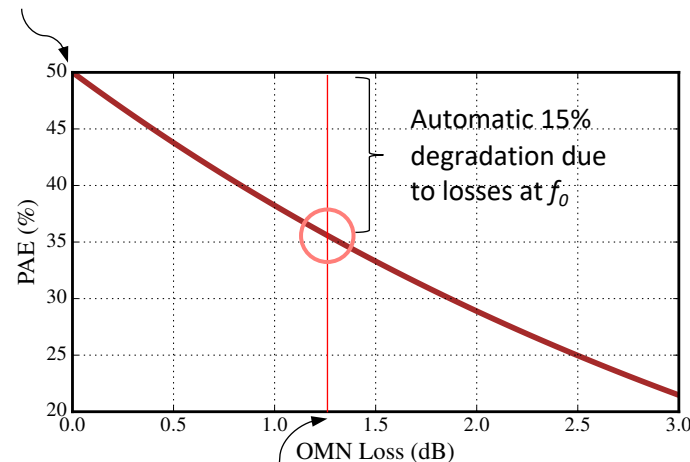
Effects of Losses at 32 GHz for a Hybrid Off-Chip Matching Approach

Develop harmonically-tuned GaN amplifier using high-Q off-chip elements

- Bond-wire interconnect from drain of GaN transistor to off-chip matching network
- Microstrip resonator matching network on standard Alumina substrate
- Custom-tuned single-layer capacitor for output DC block

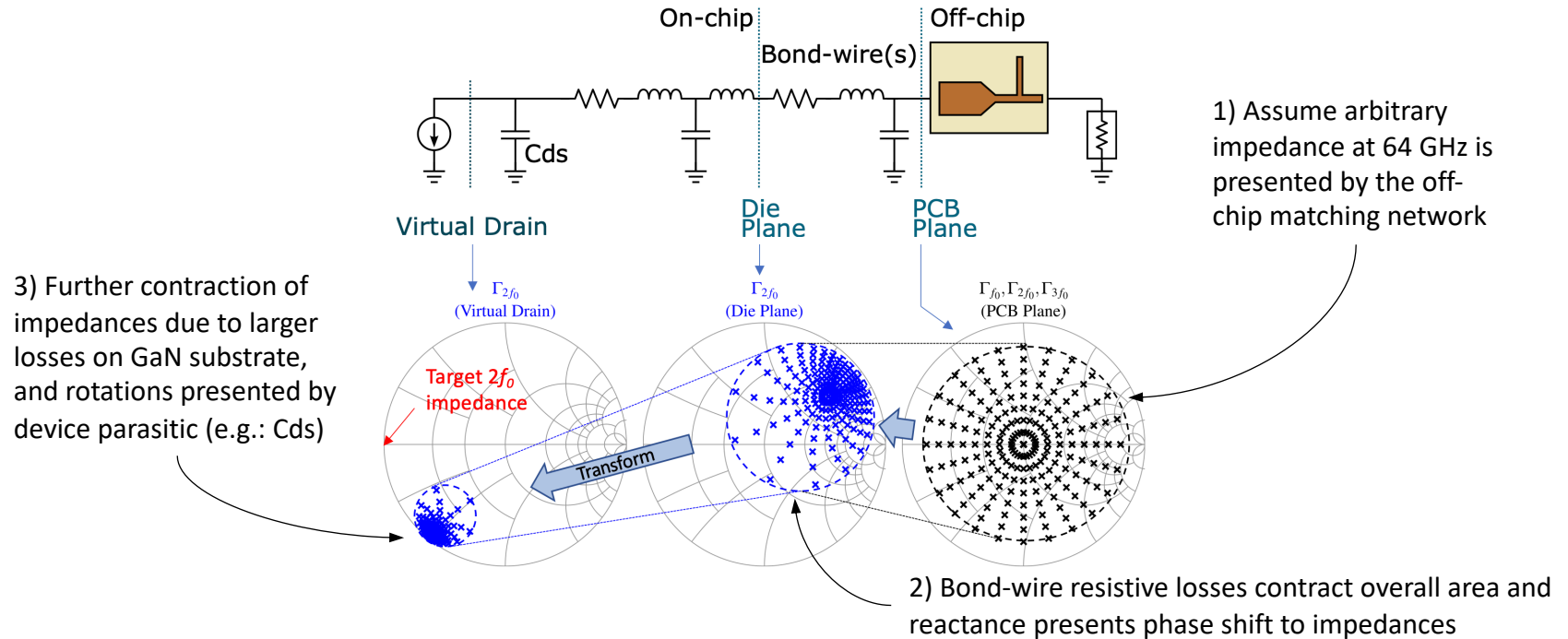


Assume device provides 50% efficiency using loss-less output matching network



Loss at f_0 for bond wire & DC block cap is already ~ 1.2 dB

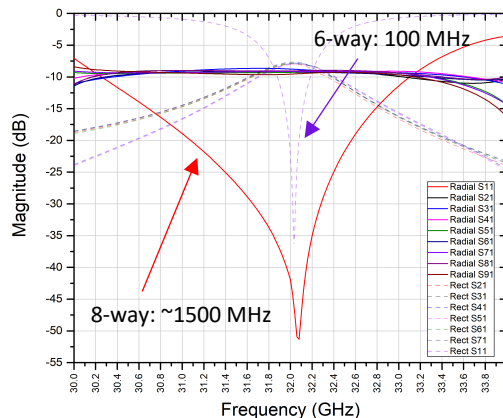
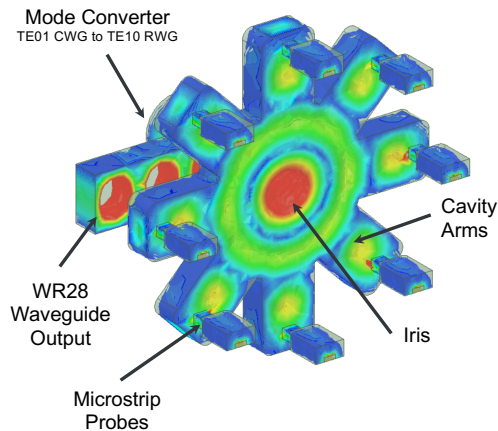
Effects of 2nd-harmonic Losses at 64 GHz for a Hybrid Off-Chip Matching Approach



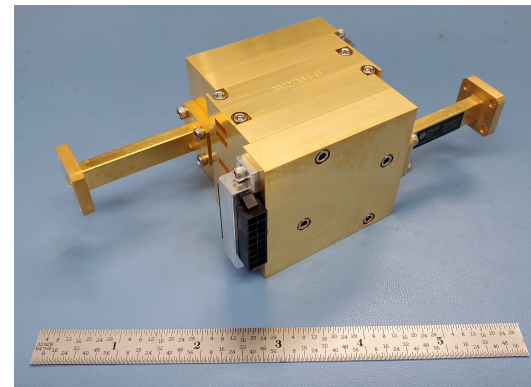
This illustrates that there is no passive impedance that can be realized in an off-chip matching network that will result in the harmonic impedances necessary for high-efficiency operation.



Spatial Power Combiner for Higher Output Power



Fabricated/Assembled Spatial Power Combiner



- Spatial combiners use waveguide modes to power combine the amplified EM waves for high output power
- Compared to the 6-way rectangular design from Year-1, a novel 8-way radial design shows significant bandwidth improvement of over 10x with low loss of approximately 0.6 dB
- Coupled with the 2.5-Watt 37%-efficient MMIC, the expected combined RF output power is 18 Watts with an overall efficiency of 32%
- Link budget using a 42-dBi antenna to a DSN station with convolutional coding shows maximum downlink rate of 700 bps can be supported with 3 dB of margin at 10 AU



- Off-chip hybrid matching for high-efficiency operation at Ka-band is not feasible, due to large losses and impedance transformations introduced by bond-wire interconnects, DC blocking capacitors, and intrinsic device parasitic of GaN transistors
- A highly-efficient (35-37% PAE) 2.5-Watt MMIC power amplifier using CREE's V5 150-nm GaN/SiC process was designed for operation in the DSN 31.8-32.3 GHz frequency band, providing significant improvement against commercially-available devices that are typically < 20% PAE
- A novel 8-way radial spatial power combiner was designed to provide low-loss power combination for the DSN 31.8-32.3 GHz frequency band
- An 18-Watt RF output, 32% overall efficiency SSPA can be expected from the combination of the 2.5-W MMIC and 8-way spatial combiner designed in this study.
- The 18-Watt SSPA coupled with a 42-dBi antenna is expected to provide over 500 bps of telemetry downlink to the DSN from a range of 10 AU (Saturn)